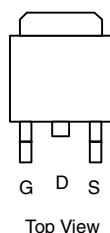


N-Channel 75 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
75	0.007 at $V_{GS} = 10$ V	110 ^d	69

TO-263



Top View

Ordering Information: SUM110N08-07P-E3 (Lead (Pb)-free)

FEATURES

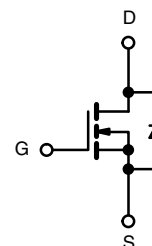
- TrenchFET® Power MOSFETS
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT

APPLICATIONS

- Synchronous Rectification



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	75	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	110 ^d
		$T_C = 70$ °C	103
Pulsed Drain Current	I_{DM}	180	A
Avalanche Current	I_{AS}	50	
Single Avalanche Energy ^a	E_{AS}	125	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	208.3 ^b
		$T_A = 25$ °C ^c	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.6	

Notes:

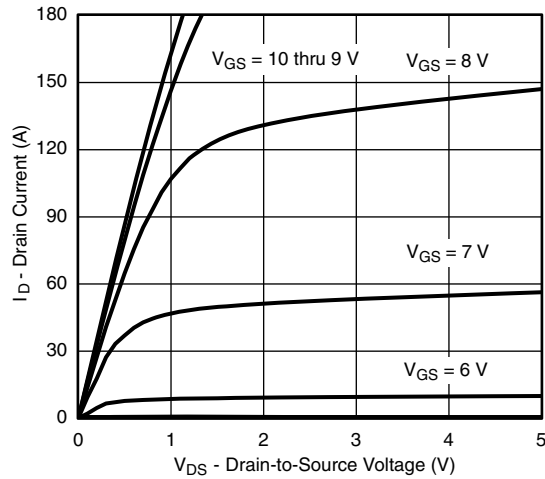
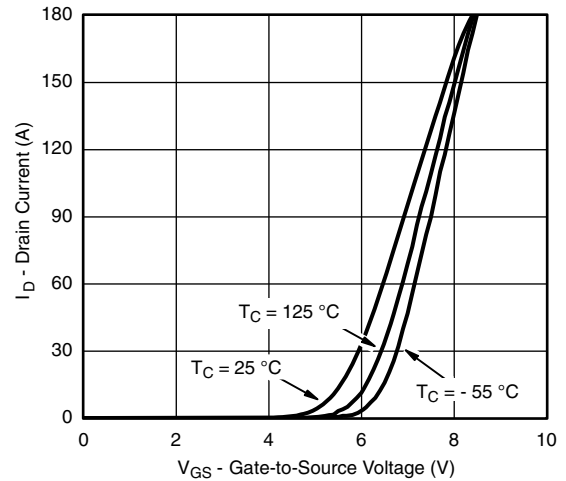
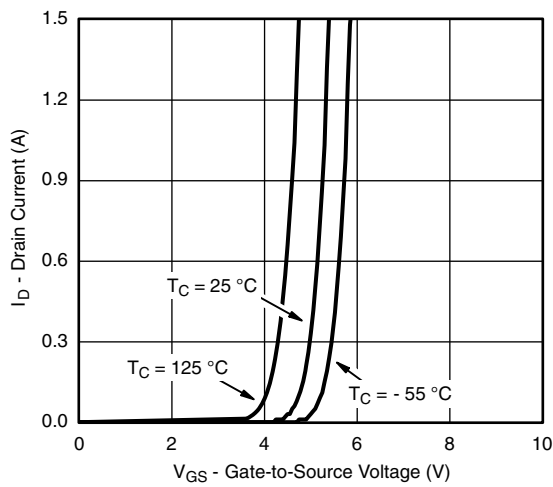
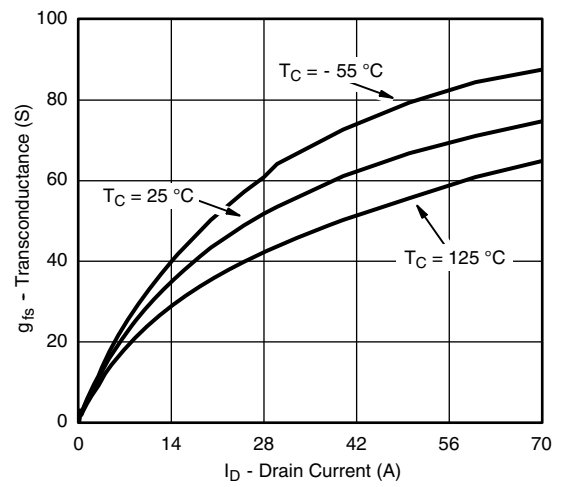
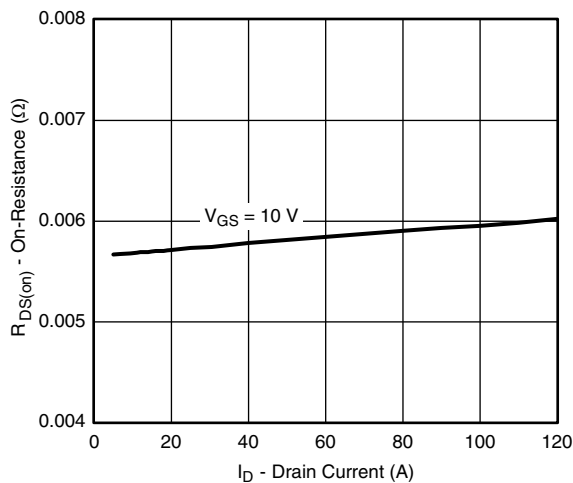
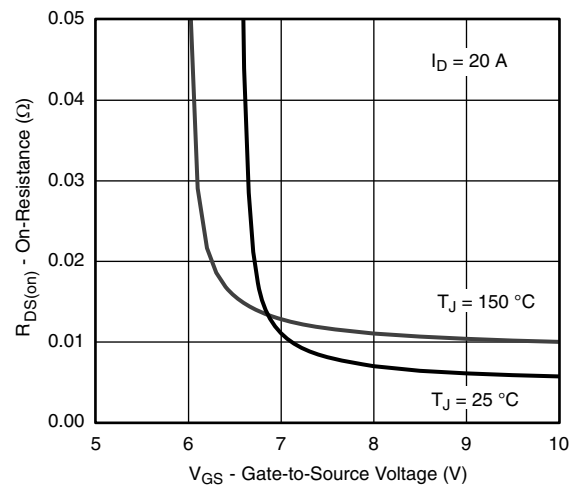
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).
- Package limited.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = 250 μA	75			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 75 V, V _{GS} = 0 V			1	μA
		V _{DS} = 75 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 75 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	70			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0057	0.0070	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.0092	0.0112	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		43		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz		4250		pF
Output Capacitance	C _{oss}			580		
Reverse Transfer Capacitance	C _{rss}			230		
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 50 A		69	105	nC
Gate-Source Charge ^c	Q _{gs}			23		
Gate-Drain Charge ^c	Q _{gd}			21		
Gate Resistance	R _g	f = 1 MHz		1.2	2.4	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.6 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 1 Ω		17	30	ns
Rise Time ^c	t _r			5	10	
Turn-Off Delay Time ^c	t _{d(off)}			22	40	
Fall Time ^c	t _f			6	15	
Source-Drain Diode Ratings and Characteristics T _C = 25 °C ^b						
Continuous Current	I _S				110	A
Pulsed Current	I _{SM}				180	
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.83	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 75 A, dI/dt = 100 A/μs		65	100	ns
Peak Reverse Recovery Current	I _{RM(REC)}			2.5	5	A
Reverse Recovery Charge	Q _{rr}				85	150

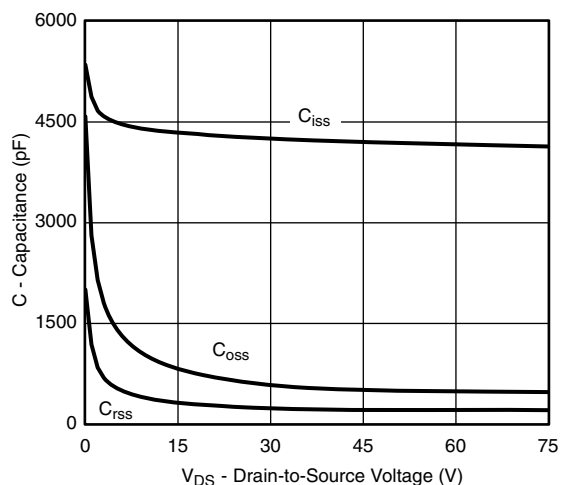
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

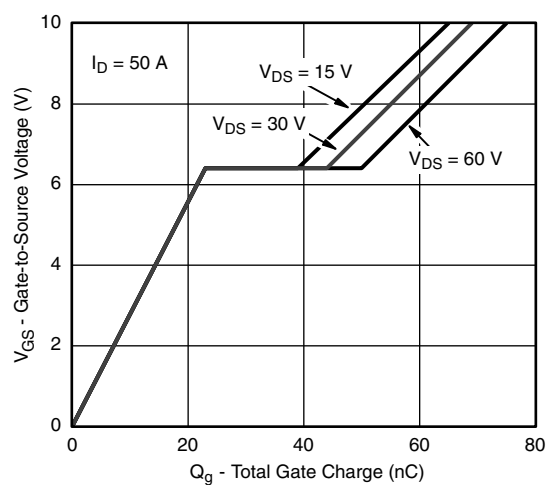
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

On-Resistance vs. Gate-to-Source Voltage

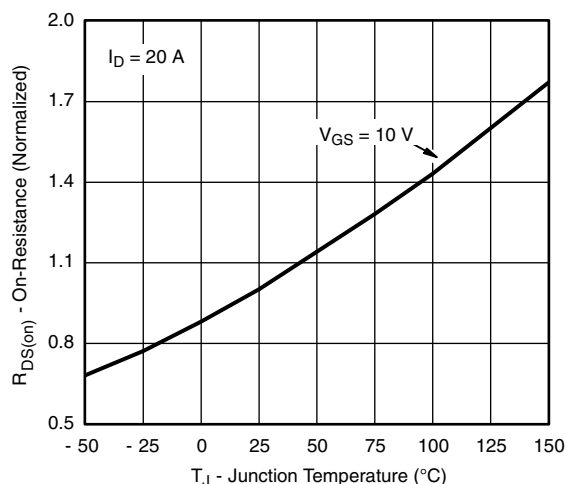
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



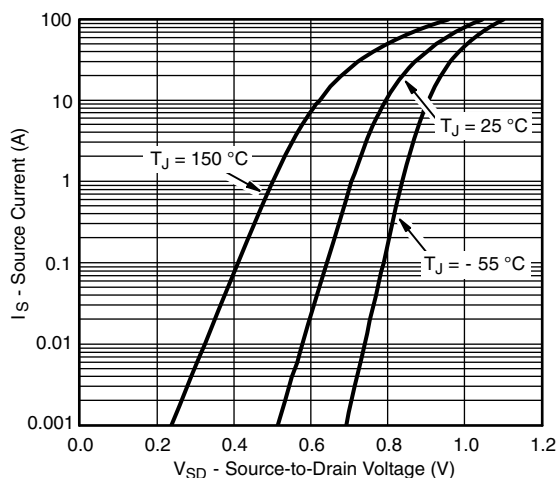
Capacitance



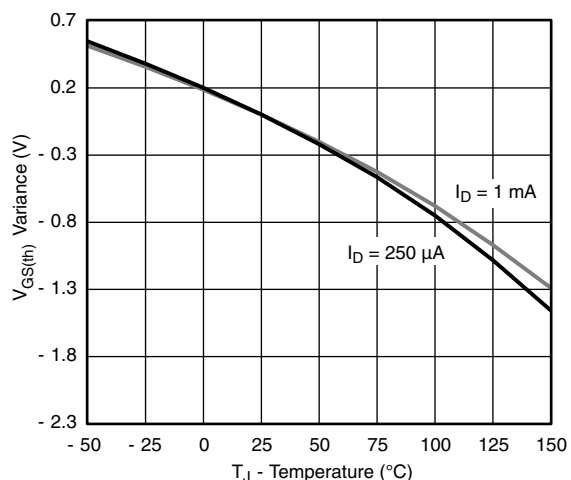
Gate Charge



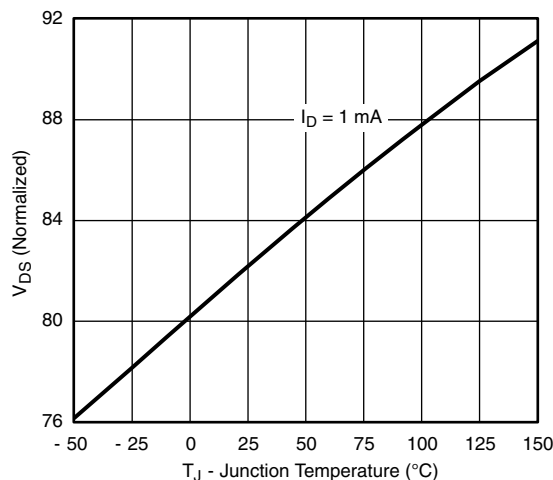
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

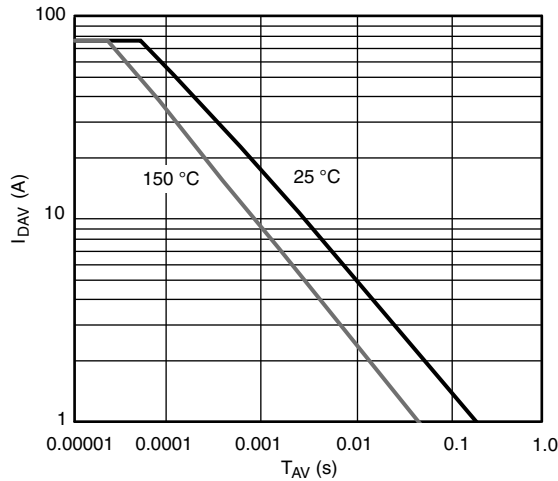


Threshold Voltage

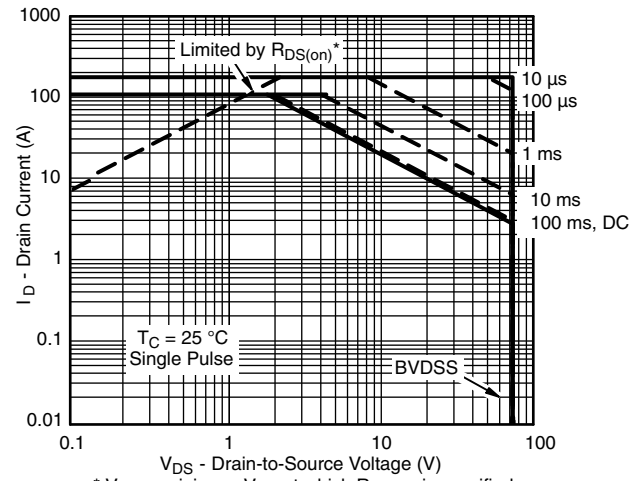


Drain Source Breakdown vs. Junction Temperature

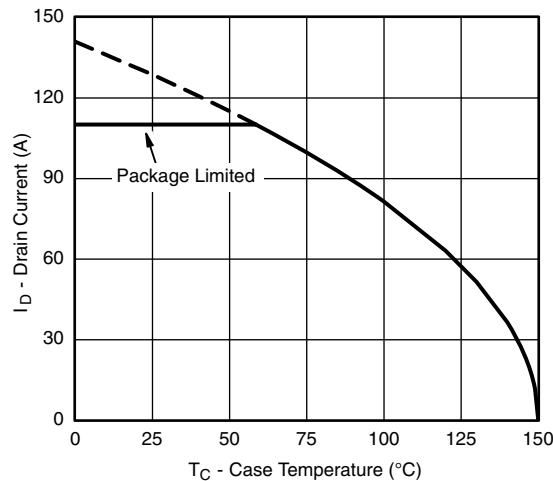
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time

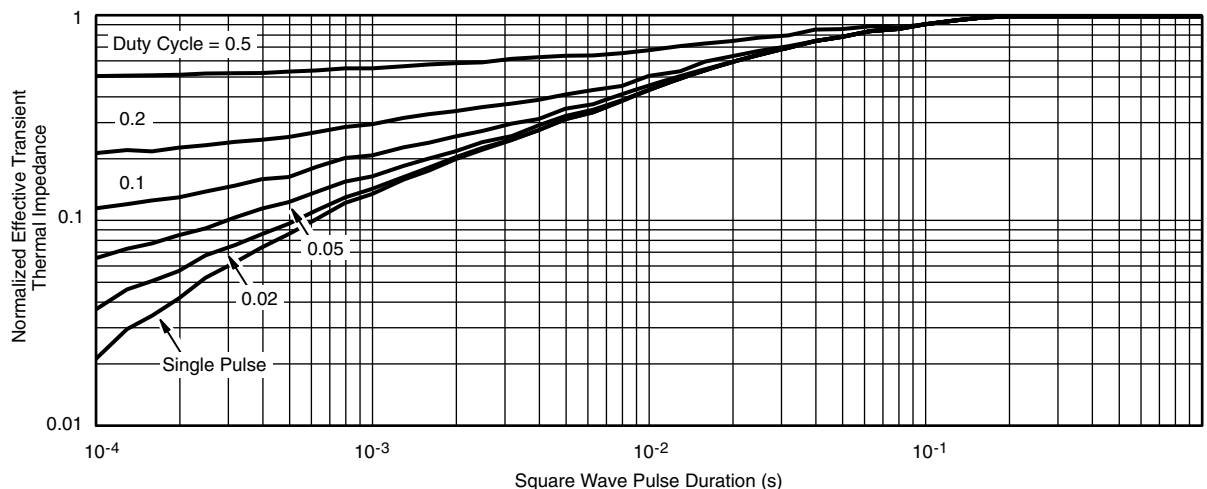


Safe Operating Area, Junction-to-Case



Current Derating*, Junction-to-Case

* The power dissipation P_D is based on $T_{J(max)} = 150 °C$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case

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